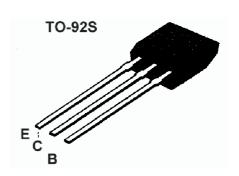
APPLICATION: General Purpose Amplify Application.

—NPN silicon —

MAXIMUM RATINGS (Ta=25℃)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	Vcbo	50	V
Collector-emitter voltage	VCEO	40	V
Emitter-base voltage	Vebo	5	V
Collector current	Ic	150	mA
Collector Power Dissipation	Pc	300	mW
Junction Temperature	Tı	150	$^{\circ}$
Storage Temperature Range	Tstg	- 55~150	$^{\circ}$



ELECTRICAL CHARACTERISTICS (Ta=25 $^{\circ}$ C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	hfe	120		820		V _{CE} = 6V, I _C = 1mA
Collector Cut-off Current	Ісво			0.5	μΑ	V _{CB} = 30V, I _E =0
Emitter Cut-off Current	Іево			0.5	μΑ	V _{EB} = 4V, Ic=0
Collector-Base Breakdown Voltage	ВУсво	50			V	Ic= 0.02mA, I _E =0
Collector-Emitter Breakdown Voltage	BVCEO	40			V	Ic= 1mA, I _B =0
Emitter-Base Breakdown Voltage	BVEBO	5			V	I _E = 0.02mA, I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.4	V	Ic= 50mA, I _B = 5mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			1.0	V	Ic= 50mA, I _B = 5mA
Gain bandwidth product	fт		180		MHz	Ic= 2mA, V _{CE} = 12V
Common Base Output Capacitance	Cob		2		PF	V _{CB} = 10V, I _E =0, f = 1MHz

$h_{FE} \ Classification$

Classification	Q	R	S	Е	
$h_{ ext{FE}}$	120~270	180~390	270~560	390~820	